

Product Summary

V_{RRM}	650 V
$I_F (T_C=140^{\circ}\text{C})$	20 A**
Q_C	60 nC**

Features

- Extremely low reverse current
- No reverse recovery current
- Temperature independent switching
- Positive temperature coefficient on V_F
- Excellent surge current capability
- Low capacitive charge

Benefits

- Essentially no switching losses
- System efficiency improvement over Si diodes
- Increased power density
- Enabling higher switching frequency
- Reduction of heat sink requirements
- System cost savings due to smaller magnetics
- Reduced EMI

Applications

- Switch mode power supplies (SMPS)
- Uninterruptible power supplies
- Motor drivers
- Power factor correction

Package Pin Definitions

- Pin1 - Anode
- Pin2 - Cathode
- Pin3 - Anode

Package Parameters

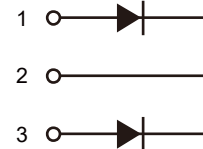
Part Number	Marking	Package
B2D20065TF	B2D20065TF	TO-3PF

* Per Leg, ** Per Device

Package: TO-3PF



Electrical Connection



Maximum Ratings ($T_c=25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter	Test conditions	Value	Unit
V_{RRM}	Repetitive peak reverse voltage		650	V
V_{RSM}	Non-repetitive peak reverse voltage		650	V
I_F	Continuous forward current	$T_c=25^\circ\text{C}$ $T_c=140^\circ\text{C}$	25*/50** 10*/20**	A
I_{FSM}	Non-repetitive forward surge current	$T_c=25^\circ\text{C}$, $t_p=10\text{ms}$ Half sine wave	70*	A
$\int i^2 dt$	i^2t value	$T_c=25^\circ\text{C}$, $t_p=10\text{ms}$	24*	A ² S
P_{tot}	Power dissipation	$T_c=25^\circ\text{C}$ $T_c=110^\circ\text{C}$	77* 33*	W
T_j	Operating junction temperature		-55~175	$^\circ\text{C}$
T_{stg}	Storage temperature		-55~175	$^\circ\text{C}$
	TO-3PF mounting torque	M3 Screw	0.6	Nm

* Per Leg, ** Per Device

Thermal Characteristics

Symbol	Parameter	Value			Unit
		Min.	Typ.	Max.	
$R_{th(jc)}$	Thermal resistance from junction to case		1.929*/ 0.965**		K/W

* Per Leg, ** Per Device

Electrical Characteristics (Per Leg)
Static Characteristics

Symbol	Parameter	Test conditions	Value			Unit
			Min.	Typ.	Max.	
V_{DC}	DC blocking voltage	$T_j=25^\circ\text{C}$	650			V
V_F	Diode forward voltage	$I_F=10\text{A } T_j=25^\circ\text{C}$ $I_F=10\text{A } T_j=175^\circ\text{C}$		1.3 1.62	1.5 2.06	V
I_R	Reverse current	$V_R=650\text{V } T_j=25^\circ\text{C}$ $V_R=650\text{V } T_j=175^\circ\text{C}$		1 20	70 200	μA

AC Characteristics

Symbol	Parameter	Test conditions	Value			Unit
			Min.	Typ.	Max.	
Q_C	Total capacitive charge	$V_R=400\text{V } T_j=25^\circ\text{C}$ $Q_C=\int_0^{V_R} C(V)dV$		30		nC
C	Total capacitance	$V_R=1\text{V } f=1\text{MHz}$ $V_R=300\text{V } f=1\text{MHz}$ $V_R=600\text{V } f=1\text{MHz}$		470 54 53		pF
E_C	Capacitance stored energy	$V_R=400\text{V}$		7		μJ

Typical Performance (Per Leg)

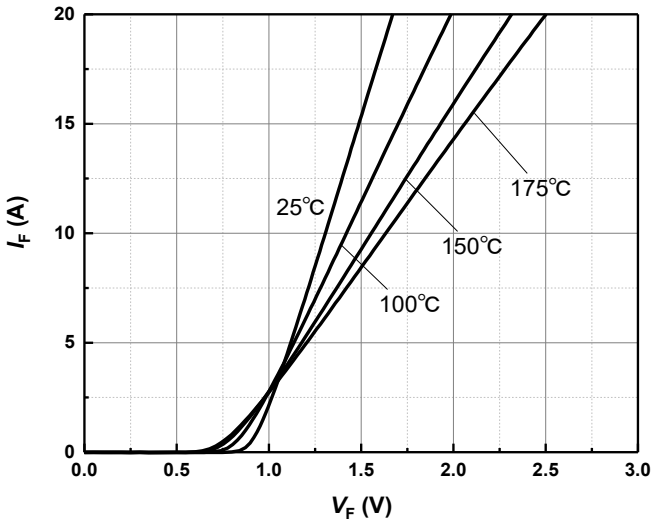


Figure 1 Typical forward characteristics

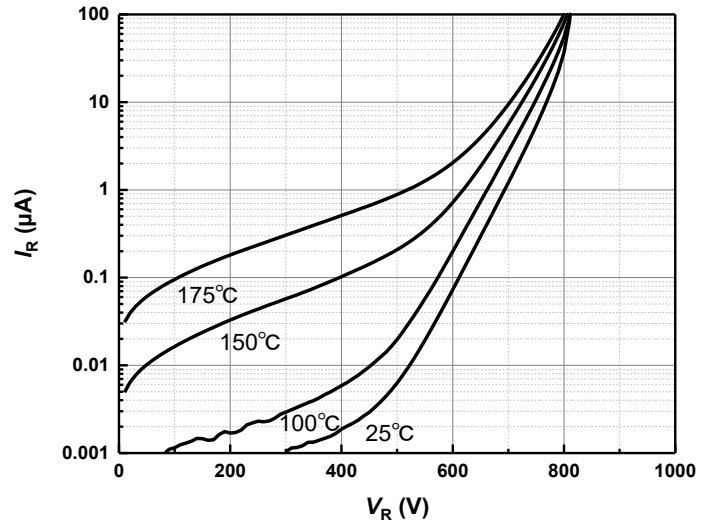


Figure 2 Typical reverse current as function of reverse voltage

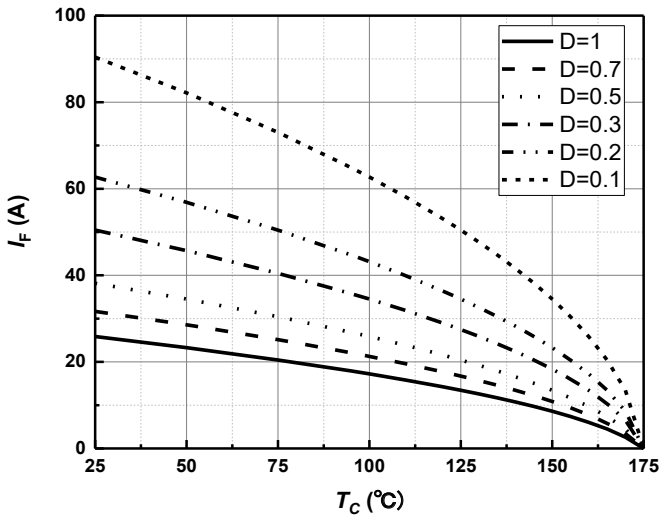


Figure 3 Diode forward current as function of temperature, D=duty cycle

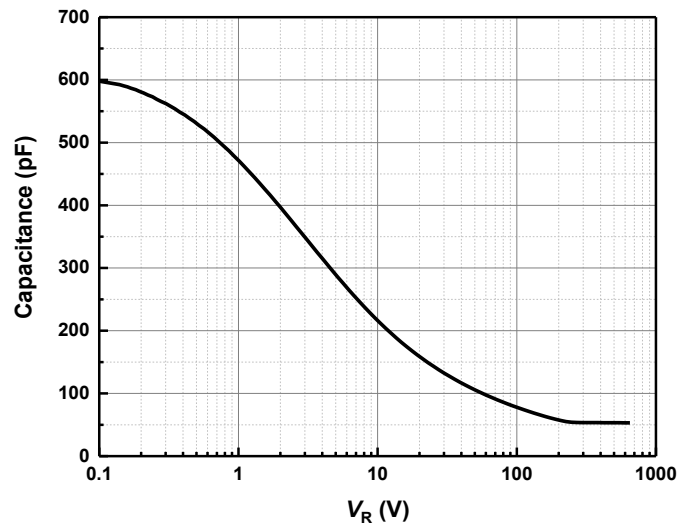


Figure 4 Typical capacitance as function of reverse voltage, $C=f(V_R)$; $T_j=25^{\circ}$ C; $f=1$ MHz

Typical Performance

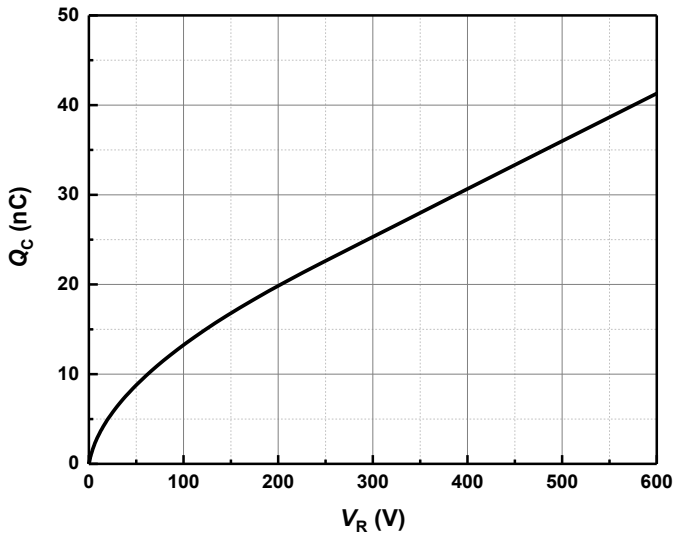


Figure 5 Typical reverse charge as function of reverse voltage

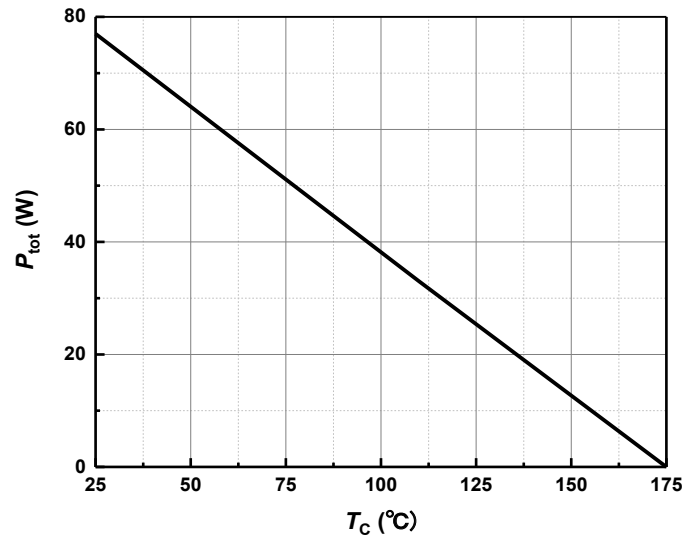


Figure 6 Power dissipation as function of case temperature

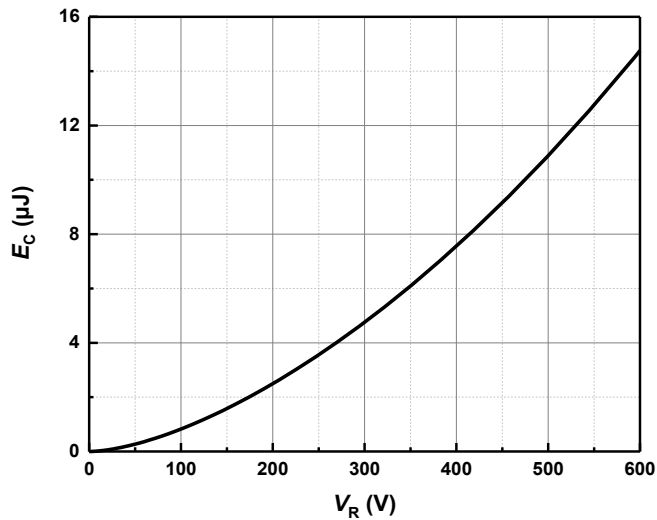


Figure 7 Capacitance stored energy

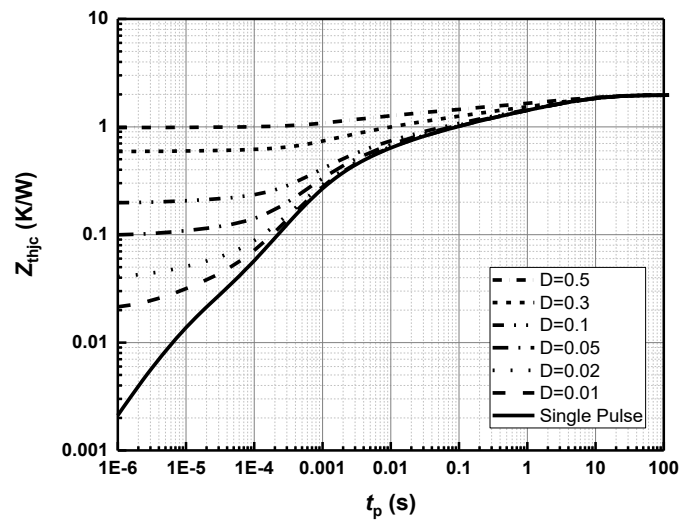
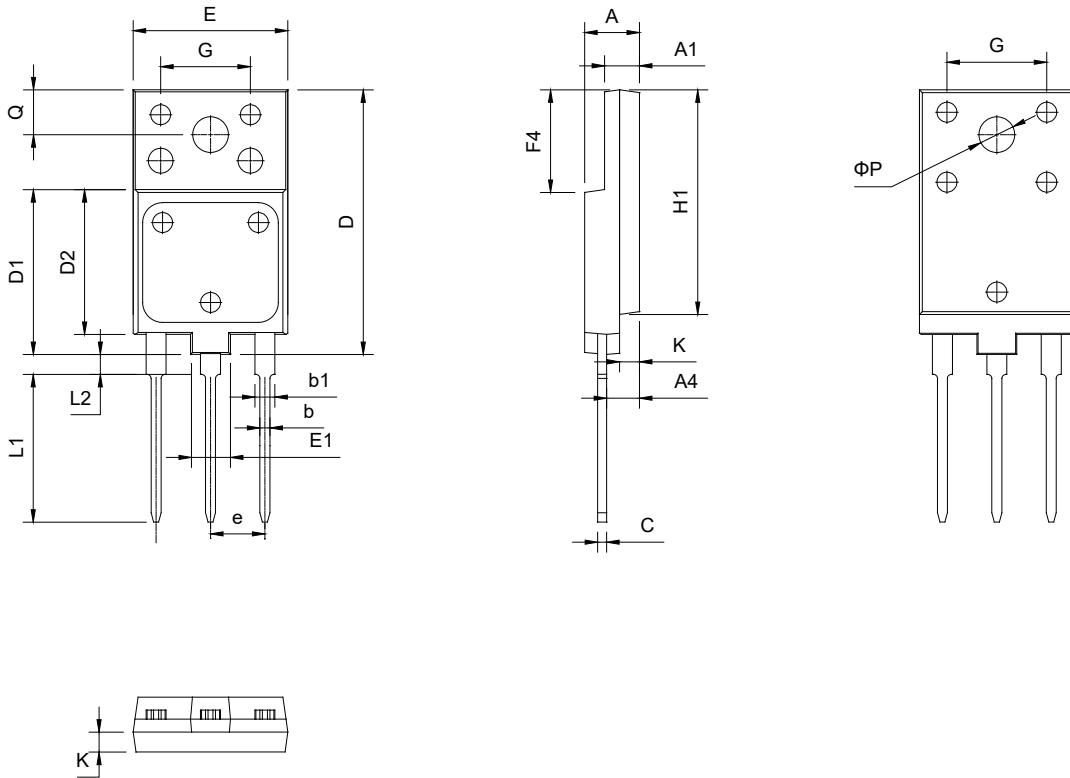


Figure 8 Max. transient thermal impedance, $Z_{thjc} = f(t)$, parameter: $D = t / T$

Package Dimensions


SYMBOL	mm		
	MIN	NOM	MAX
A	5.3	5.5	5.7
A1	2.8	3	3.2
b	0.66	0.86	0.95
b1	1.8	2	2.2
A4	3.1	3.3	3.5
C	0.8	0.9	1
D	26.3	26.5	26.7
D1	16.3	16.5	16.7
D2	14.3	14.5	14.7
P	3.4	3.6	3.8
E	15.3	15.5	15.7
E1	3.8	4	4.2
e	5.15	5.45	5.75
G	9.7	9.9	10.1
Q	4.35	4.5	4.65
L1	14.6	14.8	15
L2	2.3	2.5	2.7
K	1.8	2	2.2
F4	9.8	10	10.2
H1	22.8	23	23.2
K	1.8	2	2.2

Revision History

Document Version	Date of Release	Description of Changes
Rev 0.0	2022-01-06	Release of the datasheet.

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Shenzhen, China
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